

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	$I_D$ Max $T_A = +25^\circ C$
-30V	19m $\Omega$ @ $V_{GS} = -10V$	-8.6A
	45m $\Omega$ @ $V_{GS} = -4.5V$	-5.5A

## Description and Applications

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

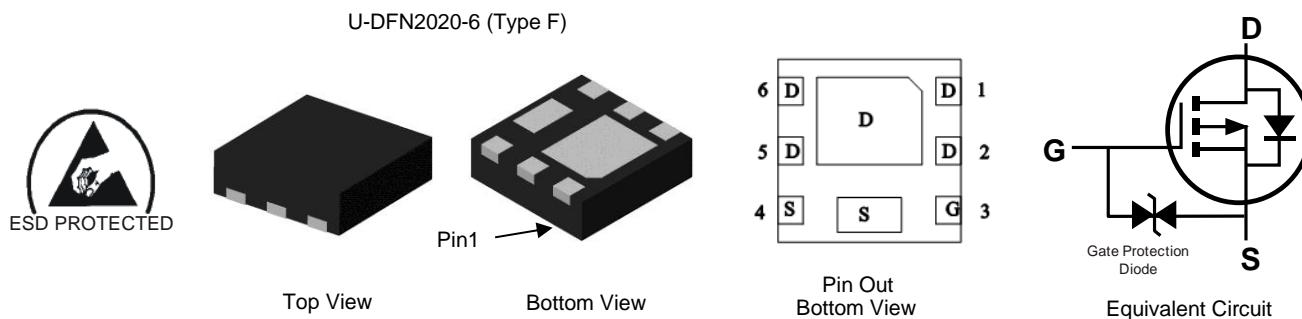
- Battery Management Application
- Power Management Functions
- DC-DC Converters

## Features and Benefits

- 0.6mm Profile – Ideal For Low Profile Applications
- Low Gate Threshold Voltage
- Low On-Resistance
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## Mechanical Data

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (Note 4)
- Weight: 0.007 grams (Approximate)



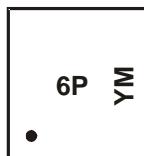
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3026SFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMP3026SFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



6P = Product Type Marking Code

YM = Date Code Marking

Y = Year (ex: D = 2016)

M = Month (ex: 9 = September)

Date Code Key

Year	2016	2017	2018	2019	2020	2021	2022	2023				
Code	D	E	F	G	H	I	J	K				
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	-30	V
Gate-Source Voltage			$V_{GSS}$	$\pm 25$	V
Continuous Drain Current (Note 6) $V_{GS} = -10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	-8.6 -6.9	A
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	$I_D$	-10.3 -8.3	A
Pulsed Drain Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)			$I_{DM}$	-50	A
Continuous Source-Drain Diode Current (Note 6)		$T_A = +25^\circ\text{C}$	$I_S$	-2.0	A
Avalanche Current (Note 7) $L = 0.1\text{mH}$			$I_{AS}$	-23	A
Avalanche Energy (Note 7) $L = 0.1\text{mH}$			$E_{AS}$	27	mJ

**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$	$P_D$	0.71	W
	$T_A = +70^\circ\text{C}$		0.47	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	178	°C/W
	$t < 10\text{s}$		125	
Total Power Dissipation (Note 6)	$T_A = +25^\circ\text{C}$	$P_D$	2.0	W
	$T_A = +70^\circ\text{C}$		1.3	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	62	°C/W
	$t < 10\text{s}$		43	
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{\theta JC}$	7.4	
Operating and Storage Temperature Range		$T_J, T_{STG}$	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

7.  $I_{AS}$  and  $E_{AS}$  rating are based on low frequency and duty cycles to keep  $T_J = +25^\circ\text{C}$ .

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 8)						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	-30	—	—	V	$\text{V}_{\text{GS}} = 0\text{V}$ , $\text{I}_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	$\text{I}_{\text{DSS}}$	—	—	-1	$\mu\text{A}$	$\text{V}_{\text{DS}} = -24\text{V}$ , $\text{V}_{\text{GS}} = 0\text{V}$
Zero Gate Voltage Drain Current $T_J = +150^\circ\text{C}$ (Note 9)		—	—	-100		
Gate-Source Leakage	$\text{I}_{\text{GSS}}$	—	—	$\pm 10$	$\mu\text{A}$	$\text{V}_{\text{GS}} = \pm 25\text{V}$ , $\text{V}_{\text{DS}} = 0\text{V}$
<b>ON CHARACTERISTICS</b> (Note 8)						
Gate Threshold Voltage	$\text{V}_{\text{GS(TH)}}$	-1	—	-3	V	$\text{V}_{\text{DS}} = \text{V}_{\text{GS}}$ , $\text{I}_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$\text{R}_{\text{DS(ON)}}$	—	15	19	$\text{m}\Omega$	$\text{V}_{\text{GS}} = -10\text{V}$ , $\text{I}_D = -4.5\text{A}$
			28	45		$\text{V}_{\text{GS}} = -4.5\text{V}$ , $\text{I}_D = -3.5\text{A}$
			34	54		$\text{V}_{\text{GS}} = -4.0\text{V}$ , $\text{I}_D = -3.0\text{A}$
Diode Forward Voltage	$\text{V}_{\text{SD}}$	—	-0.7	-1.2	V	$\text{V}_{\text{GS}} = 0\text{V}$ , $\text{I}_S = -1.0\text{A}$
<b>DYNAMIC CHARACTERISTICS</b> (Note 9)						
Input Capacitance	$\text{C}_{\text{ISS}}$	—	1,204	—	pF	$\text{V}_{\text{DS}} = -15\text{V}$ , $\text{V}_{\text{GS}} = 0\text{V}$ , $f = 1.0\text{MHz}$
Output Capacitance	$\text{C}_{\text{OSS}}$	—	154	—		
Reverse Transfer Capacitance	$\text{C}_{\text{RSS}}$	—	112	—		
Gate Resistance	$\text{R}_{\text{G}}$	—	16	—	$\Omega$	$\text{V}_{\text{DS}} = 0\text{V}$ , $\text{V}_{\text{GS}} = 0\text{V}$ , $f = 1\text{MHz}$
Total Gate Charge ( $\text{V}_{\text{GS}} = -10\text{V}$ )	$\text{Q}_{\text{G}}$	—	19.6	—	nC	$\text{V}_{\text{DS}} = -15\text{V}$ , $\text{I}_D = -9.5\text{A}$
Total Gate Charge ( $\text{V}_{\text{GS}} = -4.5\text{V}$ )	$\text{Q}_{\text{G}}$	—	9.2	—		
Gate-Source Charge	$\text{Q}_{\text{GS}}$	—	4.3	—		
Gate-Drain Charge	$\text{Q}_{\text{GD}}$	—	3.9	—		
Turn-On Delay Time	$\text{t}_{\text{D(ON)}}$	—	5.3	—		
Turn-On Rise Time	$\text{t}_{\text{R}}$	—	23	—	ns	$\text{V}_{\text{DS}} = -15\text{V}$ , $\text{V}_{\text{GS}} = -10\text{V}$ , $\text{R}_{\text{G}} = 6\Omega$ , $\text{I}_D = -9.5\text{A}$
Turn-Off Delay Time	$\text{t}_{\text{D(OFF)}}$	—	34	—		
Turn-Off Fall Time	$\text{t}_{\text{F}}$	—	26	—		
Reverse Recovery Time	$\text{t}_{\text{RR}}$	—	10	—	$\text{ns}$	$\text{I}_{\text{F}} = -9.5\text{A}$ , $\text{di/dt} = 100\text{A}/\mu\text{s}$
Reverse Recovery Charge	$\text{Q}_{\text{RR}}$	—	3.3	—	nC	

Notes: 8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.

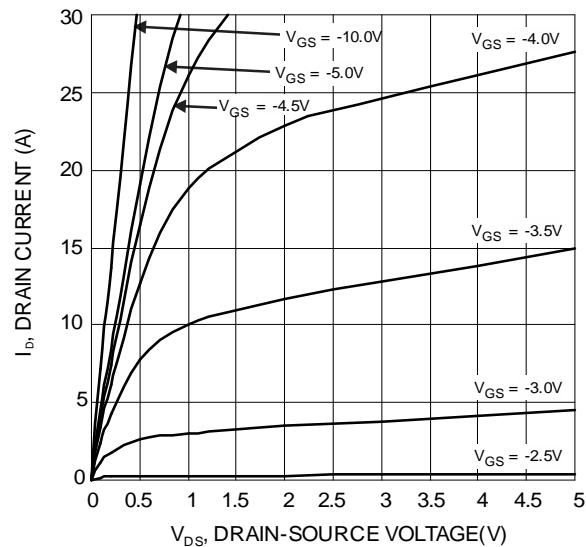


Figure 1 Typical Output Characteristic

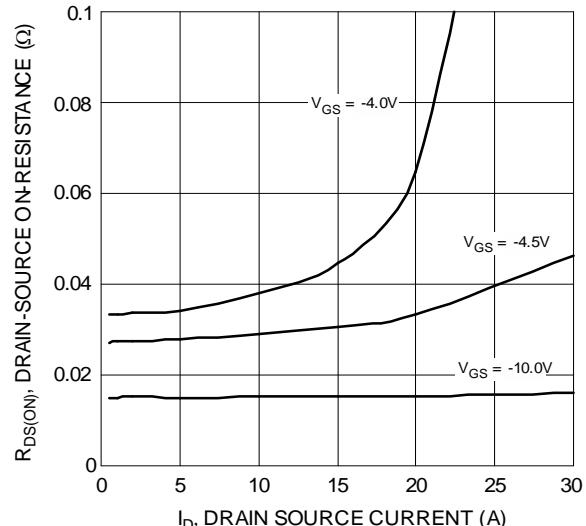


Figure 3 Typical On-Resistance vs.  
Drain Current and Gate Voltage

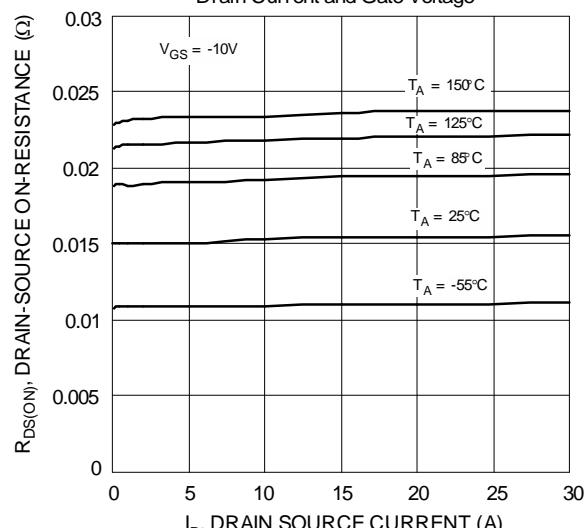


Figure 5 Typical On-Resistance vs.  
Drain Current and Temperature

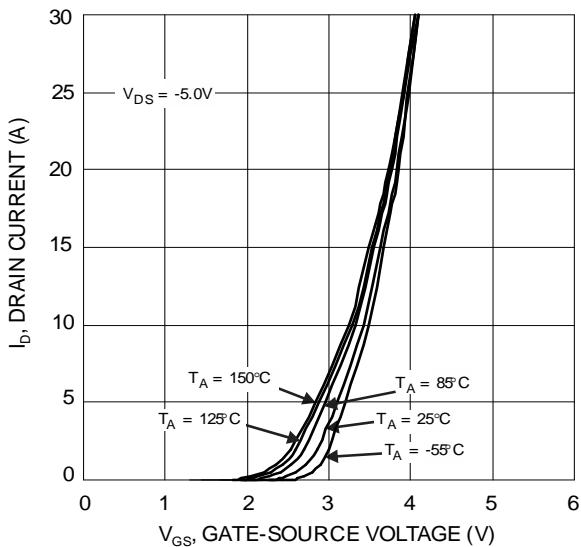


Figure 2 Typical Transfer Characteristic

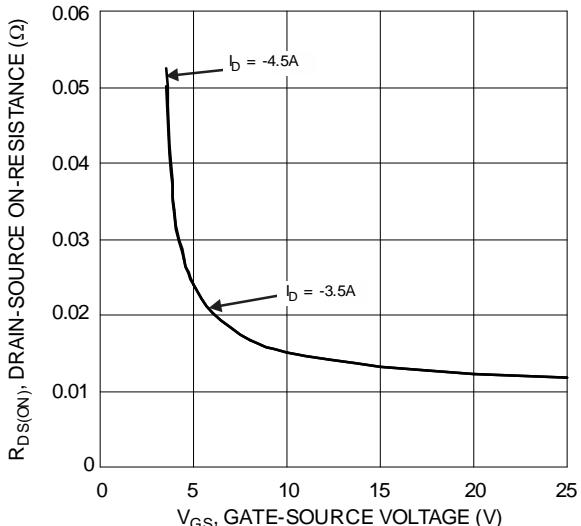


Figure 4 Typical Drain-Source On-Resistance  
vs. Gate-Source Voltage

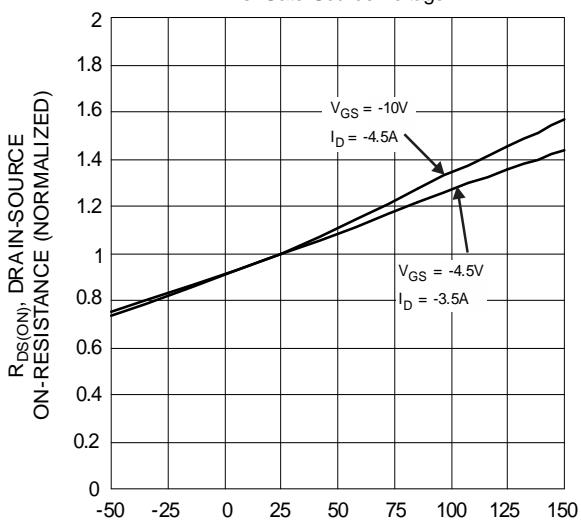


Figure 6 On-Resistance Variation with Temperature

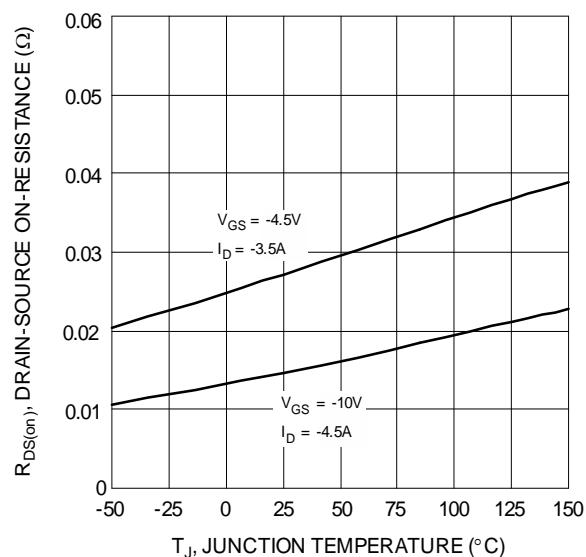


Figure 7 On-Resistance Variation with Temperature

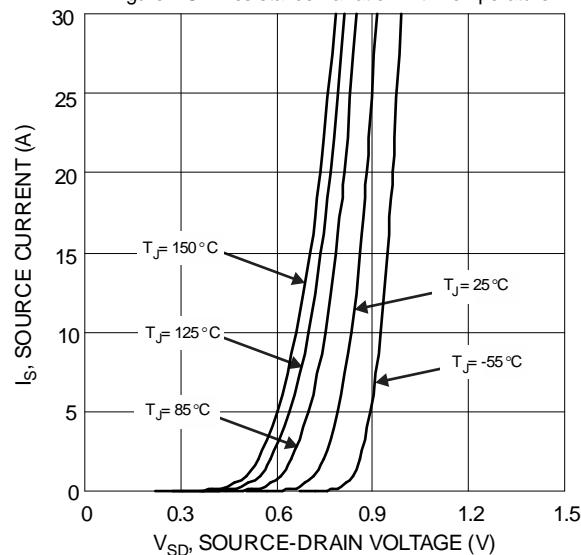


Figure 9 Diode Forward Voltage vs. Current

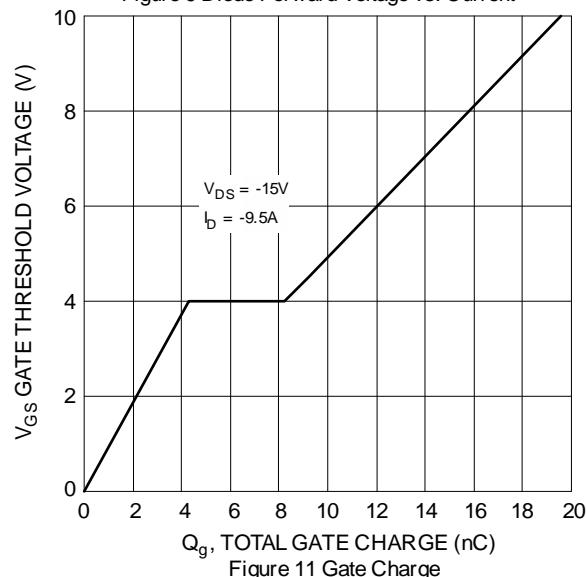


Figure 11 Gate Charge

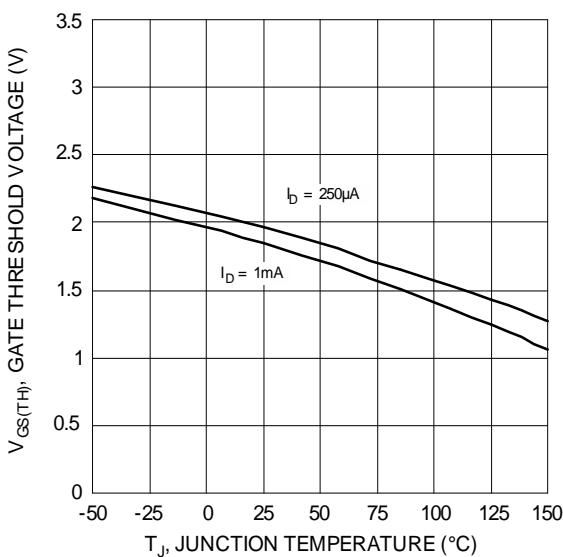


Figure 8 Gate Threshold Variation vs. Junction Temperature

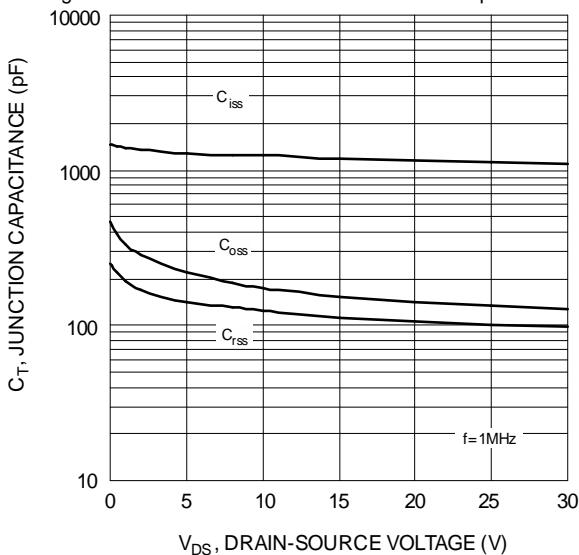


Figure 10 Typical Junction Capacitance

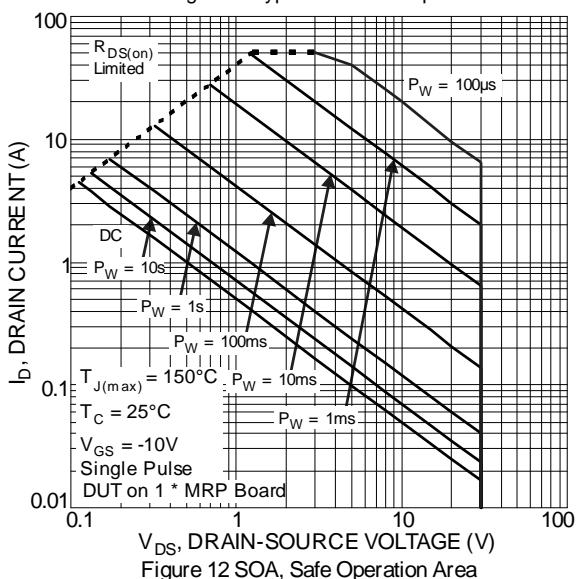


Figure 12 SOA, Safe Operation Area

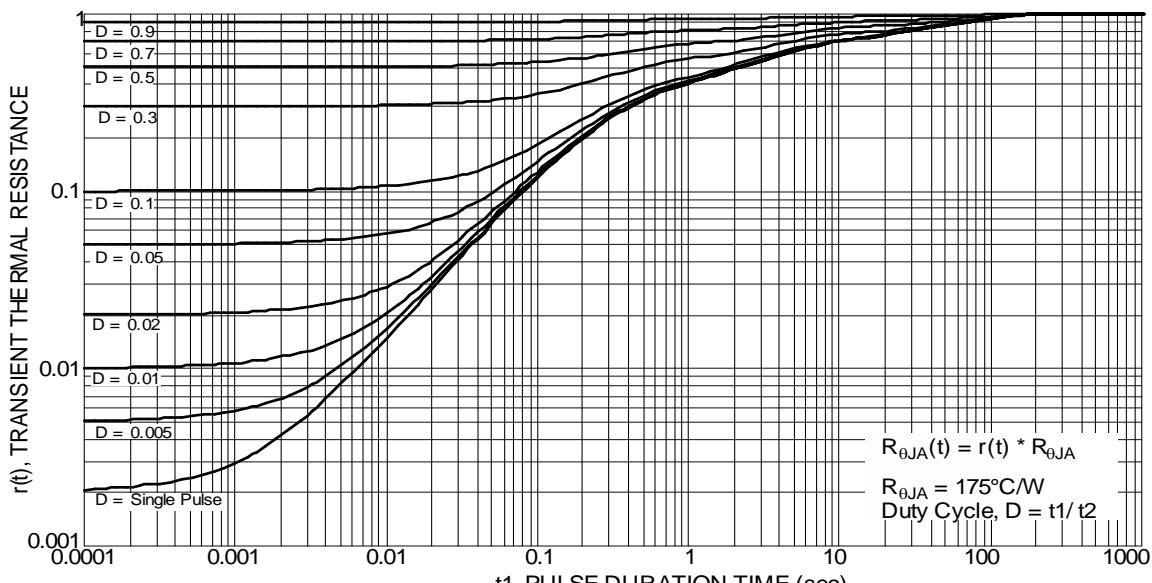
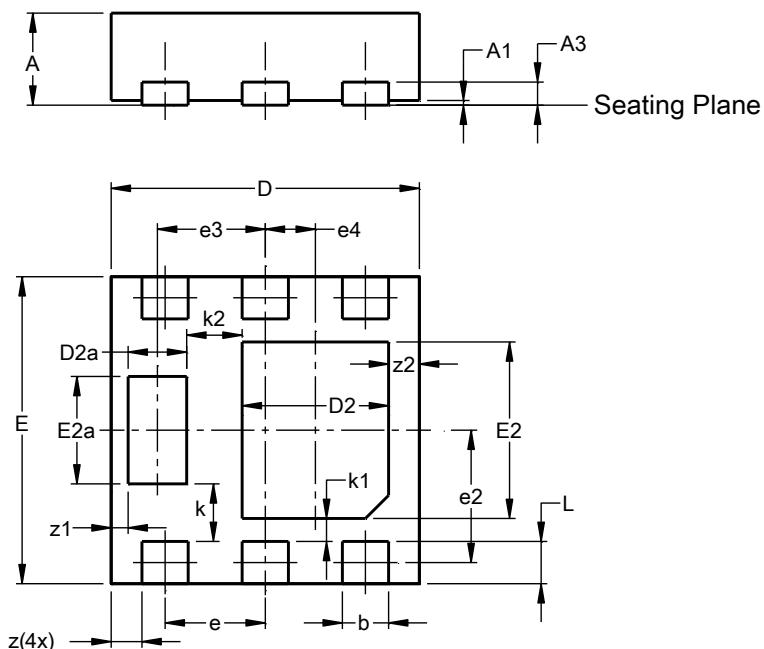


Figure 13 Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)

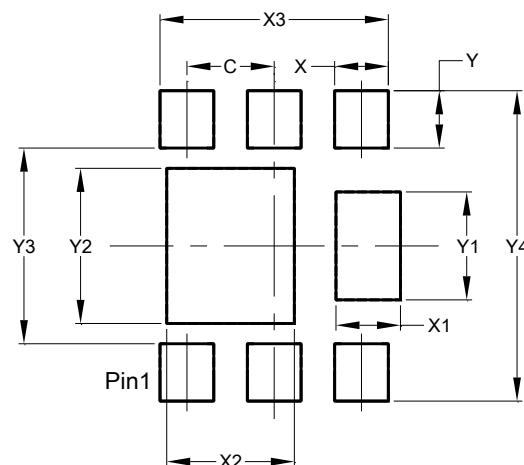


U-DFN2020-6 (Type F)			
Dim	Min	Max	Typ
<b>A</b>	0.57	0.63	0.60
<b>A1</b>	0.00	0.05	0.03
<b>A3</b>	-	-	0.15
<b>b</b>	0.25	0.35	0.30
<b>D</b>	1.95	2.05	2.00
<b>D2</b>	0.85	1.05	0.95
<b>D2a</b>	0.33	0.43	0.38
<b>E</b>	1.95	2.05	2.00
<b>E2</b>	1.05	1.25	1.15
<b>E2a</b>	0.65	0.75	0.70
<b>e</b>	0.65 BSC		
<b>e2</b>	0.863 BSC		
<b>e3</b>	0.70 BSC		
<b>e4</b>	0.325 BSC		
<b>k</b>	0.37 BSC		
<b>k1</b>	0.15 BSC		
<b>k2</b>	0.36 BSC		
<b>L</b>	0.225	0.325	0.275
<b>z</b>	0.20 BSC		
<b>z1</b>	0.110 BSC		
<b>z2</b>	0.20 BSC		
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
<b>C</b>	0.650
<b>X</b>	0.400
<b>X1</b>	0.480
<b>X2</b>	0.950
<b>X3</b>	1.700
<b>Y</b>	0.425
<b>Y1</b>	0.800
<b>Y2</b>	1.150
<b>Y3</b>	1.450
<b>Y4</b>	2.300

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